



TPV6030

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TPV6030** is Designed for Television Band IV & V Applications up to 860 MHz.

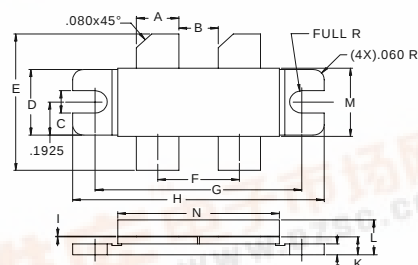
FEATURES:

- Common Emitter
- $P_G = 9.5$ dB at 35 W/860 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	15 A
V_{CEO}	28 V
V_{CBO}	55 V
V_{EBO}	4.0 V
P_{DISS}	160 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	1.1°C/W

PACKAGE STYLE .400 BAL FLG(C)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.210 / 5.33	
C	.120 / 3.05	.130 / 3.30
D	.380 / 9.65	.390 / 9.91
E	.780 / 19.81	.820 / 20.83
F	.435 / 11.05	
G	1.090 / 27.69	
H	1.335 / 33.91	1.345 / 34.16
I	.003 / 0.08	.007 / 0.18
J	.060 / 1.52	.070 / 1.78
K	.082 / 2.08	.100 / 2.54
L		.205 / 5.21
M	.395 / 10.03	.407 / 10.34
N	.850 / 21.59	.870 / 22.10

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 35$ mA		55			V
BV_{CER}	$I_C = 35$ mA	$R_{BE} = 75\ \Omega$	40			V
BV_{EBO}	$I_E = 10$ mA		4.0			V
I_{CER}	$V_{CE} = 30$ V	$R_{BE} = 75\ \Omega$			10	mA
h_{FE}	$V_{CE} = 10$ V	$I_C = 2.0$ A	15		100	---
C_{OB}	$V_{CB} = 28$ V	$f = 1.0$ MHz		45		pF
P_G	$V_{CC} = 25$ V	$I_C = 4.5$ A	95	10.5		dB
IMD	$P_{OUT} = 20$ W	$f = 860$ MHz		-52	-51	dBc
P_{OUT}	$V_{CE} = 25$ V	$I_C = 4.5$ A	35	40		W